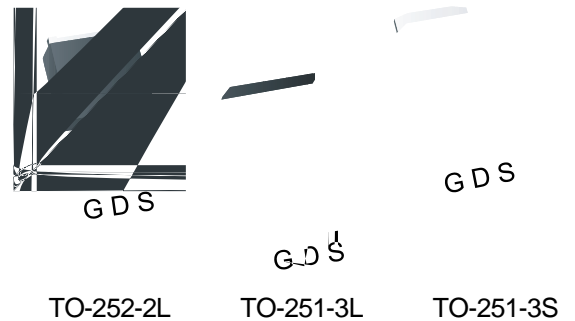


P-Channel Enhancement Mode MOSFET

Feature

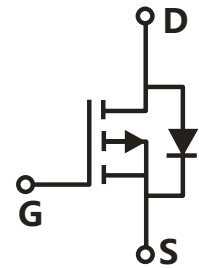
- -30V/-120A
 $R_{DS(ON)} = 4.1\ m\ (typ.)\ @V_{GS} = -10V$
 $R_{DS(ON)} = 6.5\ m\ (typ.)\ @V_{GS} = -4.5V$
- 100% Avalanche Tested
- 100% DVDS
- Reliable and Rugged
- Halogen Free and Green Devices Available
 (RoHS Compliant)

Pin Description






Applications

- Switching application
- Li-battery protection
- Motor control



Single P-Channel MOSFET

Ordering and Marking Information

 D HYG045P03 XYMXXXXXX	 U HYG045P03 XYMXXXXXX	 V HYG045P03 XYMXXXXXX	Package Code D: TO-252-2L U: TO-251-3L V: TO-251-3S Date Code XYMXXXXXX
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Note: HUAYI halogen free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI halogen free products meet or exceed the halogen free requirements of IPC/JEDEC J-STD-020 for MSL classification at halogen free peak reflow temperature. HUAYI defines "Green" to mean halogen free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings (Tc=25°C)			

Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG045P03LQ2			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	4.4	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-25V, Frequency=1MHz	-	4552	-	pF
C _{oss}	Output Capacitance					
C _{rss}	Reverse Transfer Capacitance					
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _G =2.5 Ω, I _{DS} =-20A, V _{GS} =-10V	-	12	-	ns
T _r	Turn-on Rise Time					
t _{d(OFF)}	Turn-off Delay Time					
T _f	Turn-off Fall Time					
Gate Charge Characteristics						
Q _g	Total Gate Charge(V _{GS} =-10V)	V _{DS} =-24V, I _{DS} =-20A	-	109	-	nC
Q _g	Total Gate Charge(V _{GS} =-4.5V)		-	56	-	
Q _{gs}	Gate-Source Charge		-	17	-	
Q _{gd}	Gate-Drain Charge		-	30	-	
V _{plateau}	Gate plateau voltage		-	-3.3	-	V

Note: *Pulse test, pulse width 300us, duty cycle 2%

Typical Operating Characteristics

Figure 1: Power Dissipation



Figure 2: Drain Current



Figure 3: Safe Operation Area

Figure 4: Thermal Transient Impedance

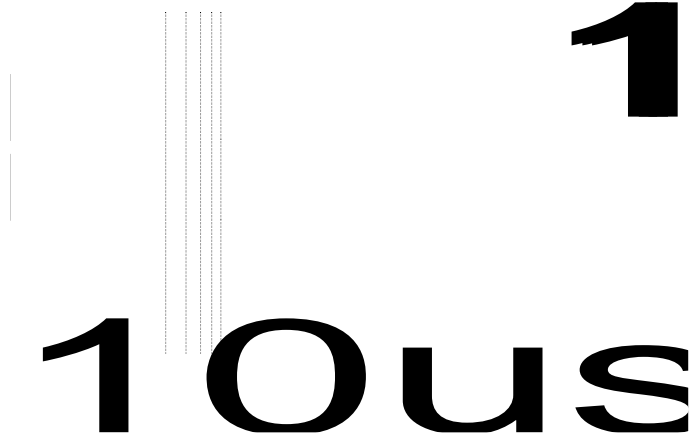


Figure 5: Output Characteristics

Figure 6: Drain-Source On Resistance

Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

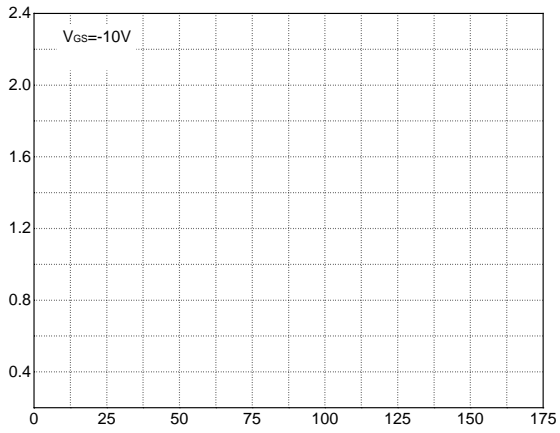


Figure 8: Source-Drain Diode Forward



Figure 9: Capacitance Characteristics

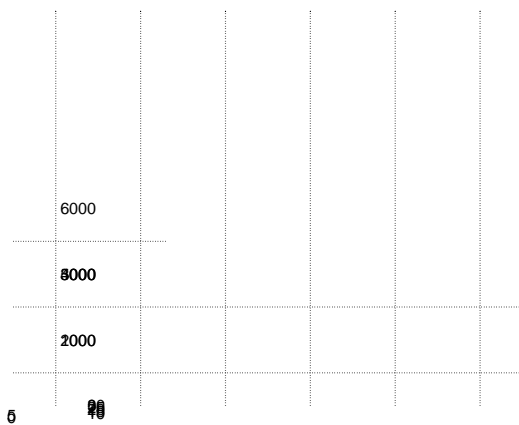
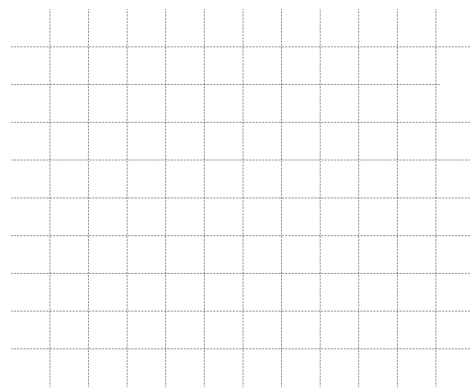
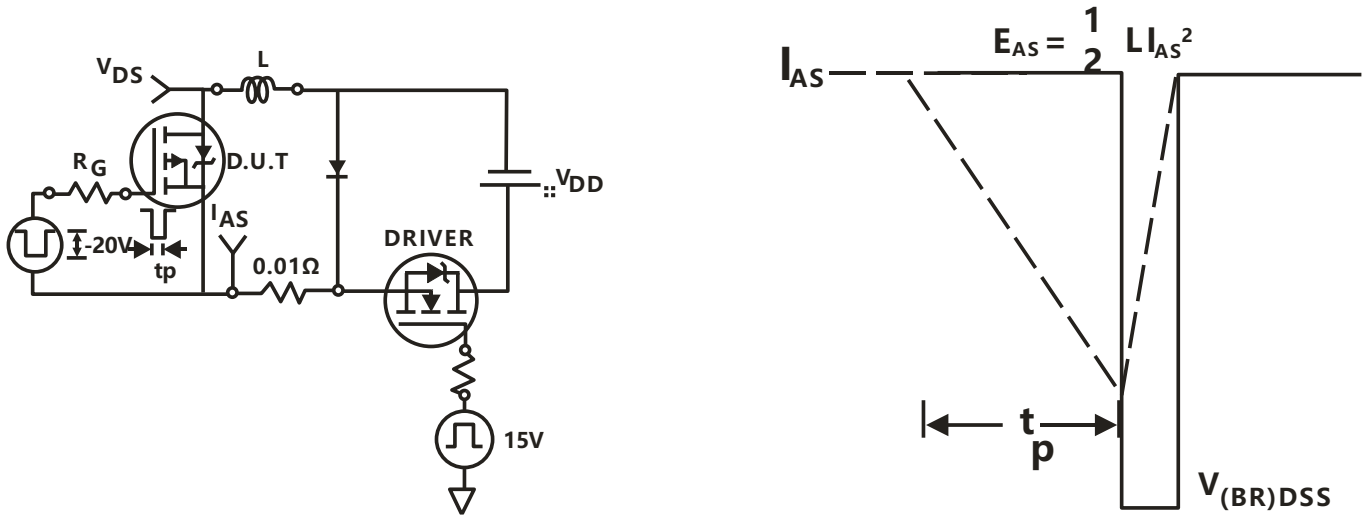


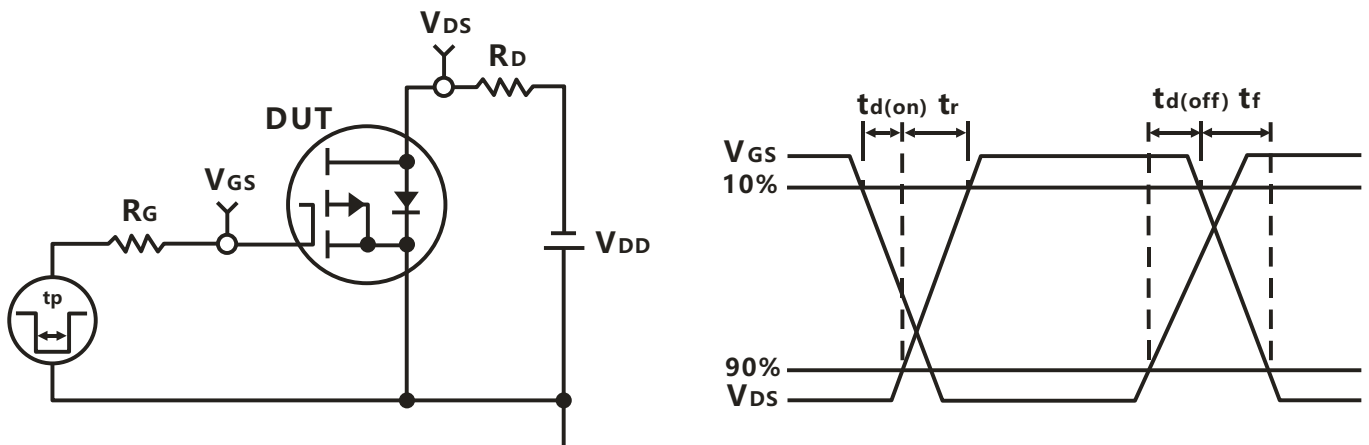
Figure 10: Gate Charge Characteristics



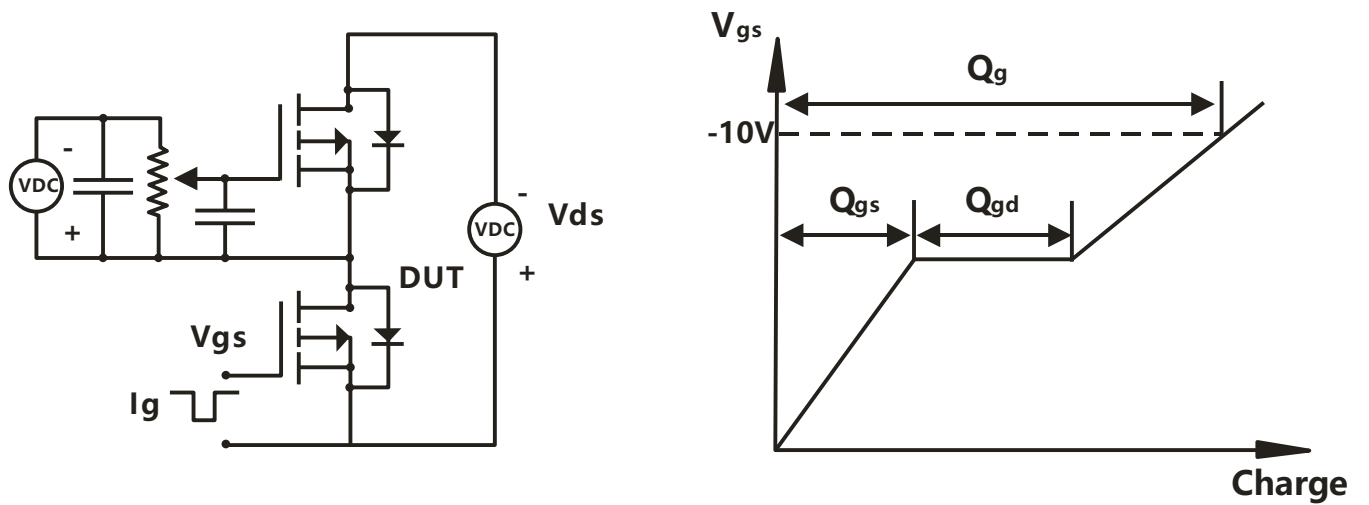
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

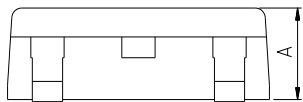
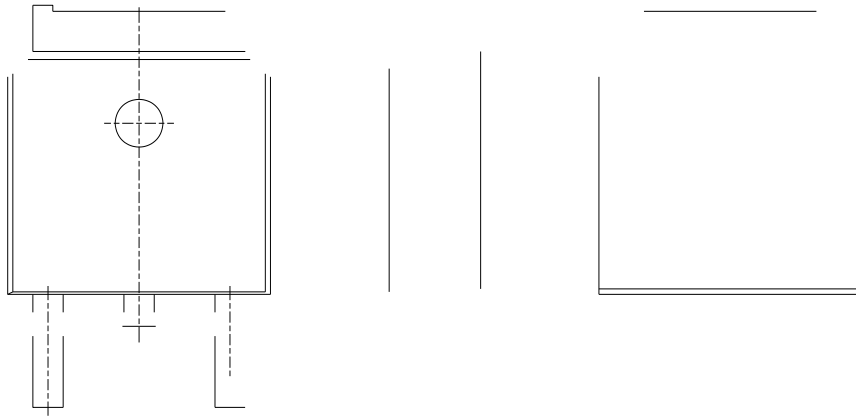


Device Per Unit

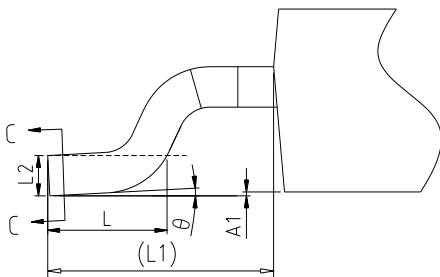
Package Type	Unit	Quantity
TO-252-2L	Tube	75
TO-252-2L	Reel	2500
TO-251-3L	Tube	75
TO-251-3S	Tube	75

Package Information

TO-252-2L

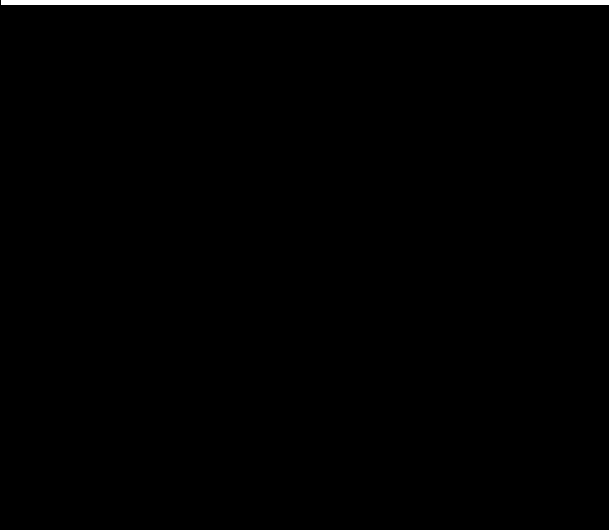


0.51BSC

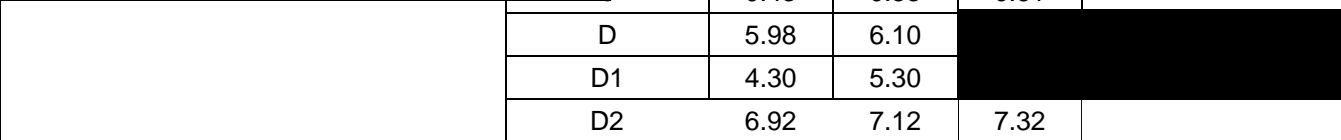
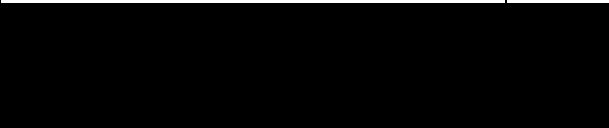


COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.12
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
	0°	-	8°

TO-251-3L



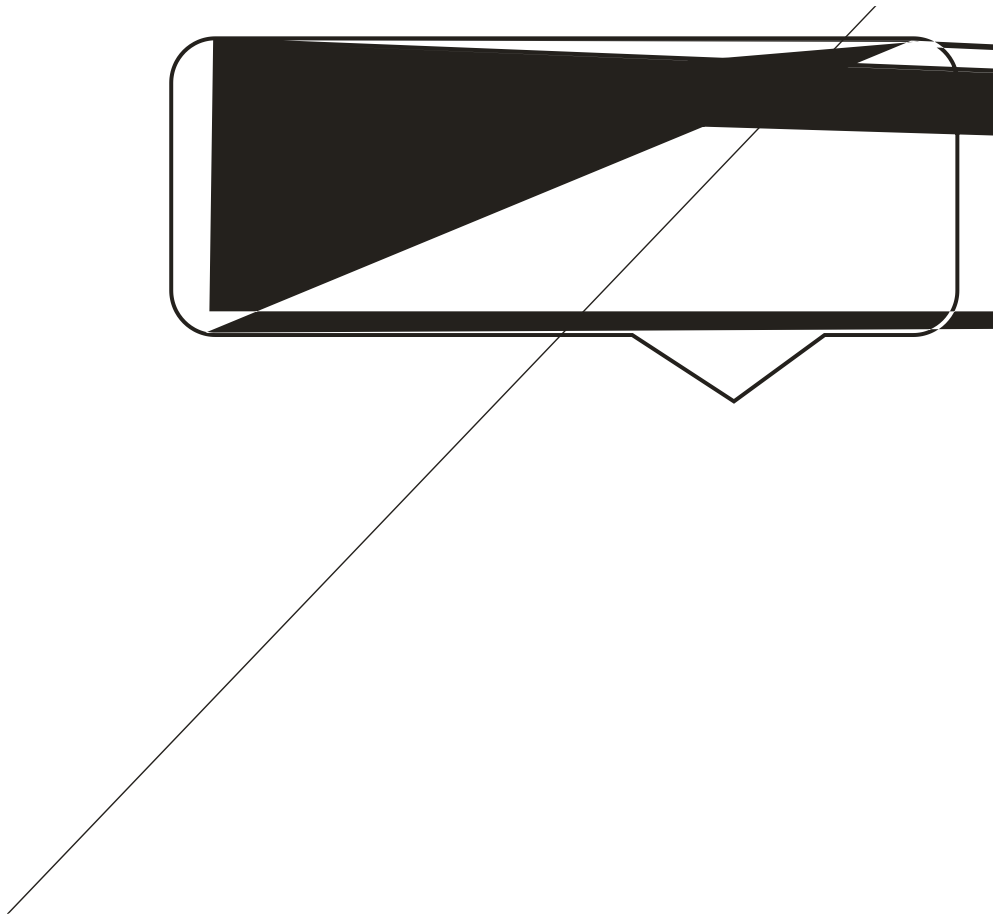
COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.46
	0.43	0.53	0.61
D	5.98	6.10	
D1	4.30	5.30	
D2	6.92	7.12	7.32



TO-251-3S

COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.60
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	10.00	11.22	11.44
L1	3.90	4.10	4.30

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum.		

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168/500 Hrs, Bias @ 150°C
HTGB	JESD-22, A108	168 /500 Hrs, V _{gs} 100% @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	250/500 Cycles, -55°C~150°C

Customer Service

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